3.2 Watt Plastic Surface Mount POWERMITE® Package

This complete new line of 3.2 Watt Zener Diodes are offered in highly efficient micro miniature, space saving surface mount with its unique heat sink design. The POWERMITE package has the same thermal performance as the SMA while being 50% smaller in footprint area and delivering one of the lowest height profiles (1.1 mm) in the industry. Because of its small size, it is ideal for use in cellular phones, portable devices, business machines and many other industrial/consumer applications.

Features

- Zener Breakdown Voltage: 6.2 47 V
- DC Power Dissipation: 3.2 W with Tab 1 (Cathode) @ 75°C
- Low Leakage < 5 μA
- ESD Rating of Class 3 (> 16 kV) per Human Body Model
- Low Profile Maximum Height of 1.1 mm
- Integral Heat Sink/Locking Tabs
- Full Metallic Bottom Eliminates Flux Entrapment
- Small Footprint Footprint Area of 8.45 mm²
- Supplied in 12 mm Tape and Reel
- Lead Orientation in Tape: Cathode (Short) Lead to Sprocket Holes
- POWERMITE is JEDEC Registered as DO-216AA
- Cathode Indicated by Polarity Band
- These Devices are Pb-Free and are RoHS Compliant

Mechanical Characteristics

CASE: Void-free, transfer-molded, thermosetting plastic

FINISH: All external surfaces are corrosion resistant and leads are

readily solderable

MOUNTING POSITION: Any

MAXIMUM CASE TEMPERATURE FOR SOLDERING PURPOSES:

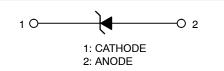
260°C for 10 Seconds



ON Semiconductor®

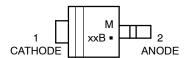
www.onsemi.com

PLASTIC SURFACE MOUNT 3.2 WATT ZENER DIODES 6.2 – 47 VOLTS





MARKING DIAGRAM



M = Date Code

xxB = Specific Device Code (See Table on Page 2)

= Pb-Free Package

ORDERING INFORMATION

Dev	vice	Package	Shipping [†]		
1PMT5	9xxBT1G	POWERMITE (Pb-Free)	3000 / Tape & Reel		

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

MAXIMUM RATINGS

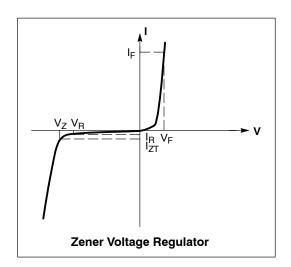
Rating	Symbol	Value	Unit
DC Power Dissipation @ T _A = 25°C (Note 1) Derate above 25°C Thermal Resistance, Junction–to–Ambient	P_{D} $R_{ hetaJA}$	500 4.0 248	mW mW/°C °C/W
Thermal Resistance, Junction-to-Lead (Anode)	$R_{ heta Janode}$	35	°C/W
Maximum DC Power Dissipation (Note 2) Thermal Resistance from Junction-to-Tab (Cathode)	$\begin{array}{c} P_D \\ R_{\thetaJcathode} \end{array}$	3.2 23	W °C/W
Operating and Storage Temperature Range	T _J , T _{stg}	-55 to +150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

- 1. Mounted with recommended minimum pad size, PC board FR-4.
- 2. At Tab (Cathode) temperature, T_{tab} = 75°C

ELECTRICAL CHARACTERISTICS ($T_L = 25^{\circ}\text{C}$ unless otherwise noted, $V_F = 1.5 \text{ V Max.}$ @ $I_F = 200 \text{ mAdc}$ for all types)

Symbol	Parameter			
V _Z	Reverse Zener Voltage @ I _{ZT}			
I _{ZT}	Reverse Current			
Z _{ZT}	Maximum Zener Impedance @ I _{ZT}			
I _{ZK}	Reverse Current			
Z _{ZK}	Maximum Zener Impedance @ I _{ZK}			
I _R	Reverse Leakage Current @ V _R			
V _R	Reverse Voltage			
IF	Forward Current			
V _F	Forward Voltage @ I _F			



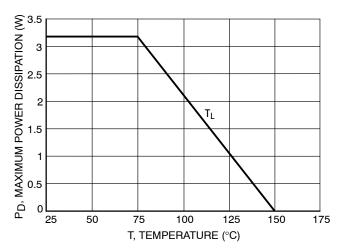
ELECTRICAL CHARACTERISTICS ($T_L = 30$ °C unless otherwise noted, $V_F = 1.25$ Volts @ 200 mA)

		Zener Voltage (Note 3)					Z _{ZT} @ I _{ZT}	Z _{ZK} @ I _{ZK}		
	Device	V _Z	V _Z @ I _{ZT} (Volts)		I _{ZT}	I _R @ V _R	V_{R}	(Note 4)	(Note 4)	I _{ZK}
Device*	Marking	Min	Nom	Max	(mA)	(μΑ)	(V)	(Ω)	(Ω)	(mA)
1PMT5920BT1G	20B	5.89	6.2	6.51	60.5	5.0	4.0	2.0	200	1.0
1PMT5921BT1G	21B	6.46	6.8	7.14	55.1	5.0	5.2	2.5	200	1.0
1PMT5924BT1G	24B	8.64	9.1	9.56	41.2	5.0	7.0	4.0	500	0.5
1PMT5927BT1G	27B	11.4	12	12.6	31.2	1.0	9.1	6.5	550	0.25
1PMT5929BT1G	29B	14.25	15	15.75	25	1.0	11.4	9.0	600	0.25
1PMT5933BT1G	33B	20.9	22	23.1	17	1.0	16.7	17.5	650	0.25
1PMT5934BT1G	34B	22.8	24	25.2	15.6	1.0	18.2	19	700	0.25
1PMT5935BT1G	35B	25.65	27	28.35	13.9	1.0	20.6	23	700	0.25
1PMT5941BT1G	41B	44.65	47	49.35	8.0	1.0	35.8	67	1000	0.25

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

- 3. Zener voltage is measured with the device junction in thermal equilibrium with an ambient temperature of 25°C.
- 4. Zener Impedance Derivation Z_{ZT} and Z_{ZK} are measured by dividing the AC voltage drop across the device by the AC current applied. The specified limits are for I_Z(ac) = 0.1 I_Z(dc) with the ac frequency = 60 Hz.

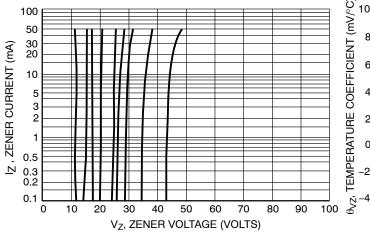
TYPICAL CHARACTERISTICS



100 (AB) 10 (B) 10 (B) 10 (C) 10 (C)

Figure 1. Steady State Power Derating

Figure 2. V_Z to 10 Volts



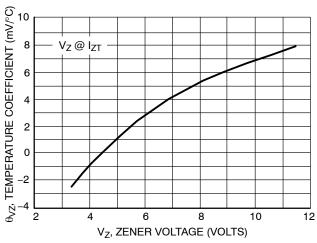
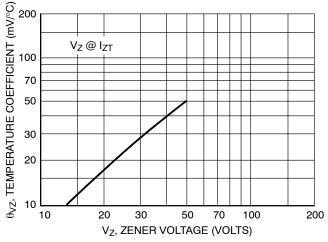


Figure 3. V_Z = 12 thru 47 Volts

Figure 4. Zener Voltage – To 12 Volts



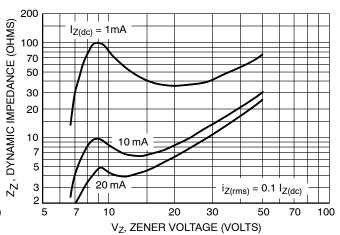


Figure 5. Zener Voltage - 14 To 47 Volts

Figure 6. Effect of Zener Voltage

TYPICAL CHARACTERISTICS

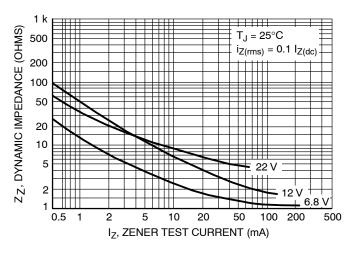


Figure 7. Effect of Zener Current

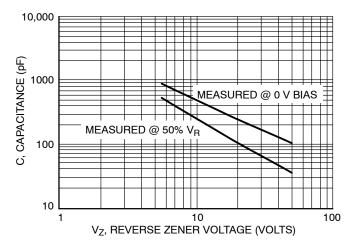
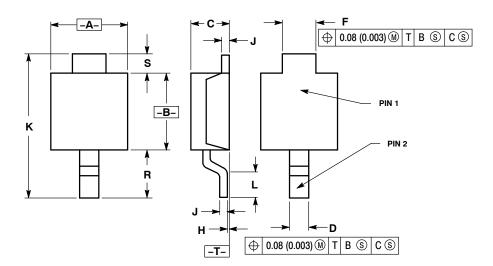


Figure 8. Capacitance versus Reverse Zener Voltage

PACKAGE DIMENSIONS

POWERMITE®

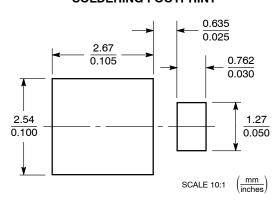
CASE 457-04 **ISSUE F**



- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ANSI
 - CONTROLLING DIMENSION: MILLIMETER
- DIMENSIONS A AND B DO NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS. MOLD FLASH, PROTRUSIONS OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.

	MILLIN	IETERS	INCHES		
DIM	MIN	MAX	MIN	MAX	
Α	1.75	2.05	0.069	0.081	
В	1.75	2.18	0.069	0.086	
С	0.85	1.15	0.033	0.045	
D	0.40	0.69	0.016	0.027	
F	0.70	1.00	0.028	0.039	
Н	-0.05	+0.10	-0.002	+0.004	
J	0.10	0.25	0.004	0.010	
K	3.60	3.90	0.142	0.154	
L	0.50	0.80	0.020	0.031	
R	1.20	1.50	0.047	0.059	
S	0.50	REF	0.019 REF		

SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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